L Number	Hits	Search t		Time stamp
1	1	6255698.pn.	USPAT	2002/09/25
2	45	isolation with trench with etch with rate	USPAT	09:45 2002/09/25
3	0	isolation with trench with etch with cost	USPAT	09:49 2002/09/25 09:49
4	4	isolation with trench with etch\$5 with cost	USPAT	2002/09/25
5	17	isolation with trench with etch\$5 with improve	USPAT	2002/09/25 09:53
6	79	trench with etch\$5 with improve	USPAT	2002/09/25 10:03
7	539	trench with etch\$5 with oxidation	USPAT	2002/09/25
8	0	trench with etch\$5 with oxidation with cost	USPAT	2002/09/25 12:30
9	5	trench with etch\$5 with oxidation with improve	USPAT	2002/09/25
10	1	trench with etch\$5 with oxidation with preferable	USPAT	2002/09/25
11	115	trench with etch\$5 with commonly	USPAT	2002/09/25 10:15
12	1	4631803.pn.	USPAT	2002/09/25 10:15
13	4	("5447887" "6140688").pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/25
-	1595	(438/427).CCLs.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/23
_	38	((438/427).CCLS.) and oxide and silicide	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/23 13:49
-	6	(((438/427).CCLS.) and oxide and silicide) and barrier	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/23 13:53
_	541	signal with line and ground with line and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/23 14:47
-	123	(signal with line and ground with line and 438/\$.ccls.) and barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/23
-	16	and 438/\$.ccls.) and barrier) and evaporation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/23
_	2	(((signal with line and ground with line and 438/\$.ccls.) and barrier) and evaporation) and (((signal with line and ground with line and 438/\$.ccls.) and barrier) and silicide) and (((signal with line and ground with line and 438/\$.ccls.) and barrier) and silane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 13:57

-	36	((signal th line and ground with line and 438/y-ccls.) and barrier) and	T;	2002/09/23 14:32
		silicide	U. GPUB; EPO; JPO;	14:32
		51110140	DERWENT;	
			IBM_TDB	
-	0	y	USPAT;	2002/09/23
		438/\$.ccls.	US-PGPUB; EPO; JPO;	14:12
			DERWENT;	
		·	IBM_TDB	
-	20	((signal with line and ground with line	USPAT;	2002/09/23
	1	and 438/\$.ccls.) and barrier) and silane	US-PGPUB; EPO; JPO;	14:10
			DERWENT;	
			IBM_TDB	
-	4		USPAT;	2002/09/23
		438/\$.ccls.	US-PGPUB; EPO; JPO;	14:14
			DERWENT;	
			IBM_TDB	
-	2	((===, ===, =====, ===== ===== ===== ======	USPAT;	2002/09/23
		silicide	US-PGPUB; EPO; JPO;	14:15
			DERWENT;	
			IBM_TDB	
-	16	((438/427).CCLS.) and metal with line	USPAT;	2002/09/23
			US-PGPUB; EPO; JPO;	14:31
			DERWENT;	
		4400 (607)	IBM_TDB	
	474	(438/627).CCLS.	USPAT;	2002/09/23
			US-PGPUB; EPO; JPO;	14:31
			DERWENT;	
_	400	///20//607\ 0070 \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	IBM_TDB	0000 (00 (00
_	423	((438/627).CCLS.) and barrier	USPAT; US-PGPUB;	2002/09/23
			EPO; JPO;	14.51
			DERWENT;	
_	26	(((438/627).CCLS.) and barrier	IBM_TDB USPAT;	2002/09/23
	20) and (((438/627).CCLS.) and evaporation)	US-PGPUB;	14:33
		and (((438/627).CCLS.) and silicide)	EPO; JPO;	
			DERWENT;	
_	61	((438/627).CCLS.) and evaporation	IBM_TDB USPAT;	2002/09/23
		(, == >, == , , =====) and ovaporation	US-PGPUB;	14:35
			EPO; JPO;	
			DERWENT; IBM TDB	
_	179	((438/627).CCLS.) and silicide	USPAT;	2002/09/23
			US-PGPUB;	14:42
			EPO; JPO;	
			DERWENT; IBM TDB	
_	150	signal with line and ground with line and	USPAT;	2002/09/23
		438/6\$2.ccls.	US-PGPUB;	14:54
			EPO; JPO;	
			DERWENT; IBM TDB	
_	14	("4252862" "5277985" "5539256"	USPAT	2002/09/23
		"5595937" "5705857" "5719447"		14:51
		"5744394" "5903053" "5909635" "5976986" "6010966" "6033986"		
		"6054380" "6080529").PN.		
_	9	("4394223" "4810332" "5071518"	USPAT	2002/09/23
		"5132775" "5272376" "5298687"		14:53
		"5326412" "5382447" "5545927").PN.		

	· · · · · · · · · · · · · · · · · · ·			
] -	115	signal v line and ground with trench	AT;	2002/09/23
			USPGPUB;	15:15
			EPO; JPO; DERWENT;	
			IBM TDB	
l <u> </u>	75	(438/42).CCLS.	USPAT;	2002/09/23
			US-PGPUB;	15:22
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	219	(438/31).CCLS.	USPAT;	2002/09/23
			US-PGPUB;	15:30
			EPO; JPO;	
			DERWENT; IBM TDB	[
_	7	("3616282" "5032220" "5121237"	USPAT	2002/09/23
		"5617493" "5834055" "5895742"	OSTAL	15:28
		"5959765").PN.		1 20120
_	111	((438/31).CCLS.) and substrate with	USPAT;	2002/09/23
		(trench hole via gap through)	US-PGPUB;	15:39
			EPO; JPO;	
			DERWENT;	
	1240		IBM_TDB	2002/02/22
_	1342	coplanar with waveguide	USPAT;	2002/09/23
			US-PGPUB; EPO; JPO;	15:38
	1		DERWENT;	
			IBM TDB	
-	665	(coplanar with waveguide) and signal and	USPAT;	2002/09/23
		ground	US-PGPUB;	15:38
			EPO; JPO;	
		· ·	DERWENT;	
	240	//	IBM_TDB	0000/00/00
-	340	((coplanar with waveguide) and signal and	USPAT;	2002/09/23
		ground) and substrate with (trench hole via gap through)	US-PGPUB; EPO; JPO;	15:40
		ta gap chitough /	DERWENT;	
			IBM TDB	
-	43	(((coplanar with waveguide) and signal	USPAT;	2002/09/23
1	1	and ground) and substrate with (trench	US-PGPUB;	15:46
		hole via gap through)) and barrier	EPO; JPO;	
1			DERWENT;	
_	32	Wayequide and migron as	IBM_TDB	2002/00/22
	32	waveguide and micron.as.	USPAT; US-PGPUB;	2002/09/23
			EPO; JPO;	13.79
			DERWENT;	
			IBM TDB	
	522	forbes and micron.as.	USPAT;	2002/09/23
			US-PGPUB;	15:50
			EPO; JPO;	
[DERWENT;	
_	236	forbes and ahn and micron.as.	IBM_TDB USPAT;	2002/00/22
<u> </u>	236	TOTMES and ann and micron.as.	USPAT; US-PGPUB;	2002/09/23
[EPO; JPO;	10.01
<u> </u>			DERWENT;	
ļ			IBM TDB	
-	52	, , = - = ,	USPAT;	2002/09/23
		signal and ground	US-PGPUB;	15:56
			EPO; JPO;	
			DERWENT;	
_	1766	wayoguido and 257/6 mala	IBM_TDB	2002/00/22
-	1756	waveguide and 257/\$.ccls.	USPAT; US-PGPUB;	2002/09/23 15:56
			EPO; JPO;	13:30
			DERWENT;	
			IBM TDB	
				

_	123	(wavegu: and 257/\$.ccls.) and signal	AT;	2002/09/23
		with ground	US PGPUB;	16:00
			EPO; JPO;	
			DERWENT;	
_	77	(369/194).CCLS.	IBM_TDB USPAT;	2002/00/22
-	''	(369/194).CCLS.		2002/09/23
			US-PGPUB; EPO; JPO;	16:02
			DERWENT;	
			IBM TDB	
_	396	coplanar with waveguide and 333/\$.ccls.	USPAT;	2002/09/23
		copiunal with waveguide and 555, v. ccis.	US-PGPUB;	16:04
1			EPO; JPO;	10.01
	1		DERWENT;	
	İ		IBM TDB	
_	173	coplanar with waveguide and silicon with	USPAT;	2002/09/23
ł		substrate	US-PGPUB;	16:22
[EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	46		USPAT;	2002/09/23
		signal and ground and silicon and oxide	US-PGPUB;	16:25
		and silane and etch	EPO; JPO;	
			DERWENT;	į
			IBM_TDB	
_	683	(438/653).CCLS.	USPAT;	2002/09/23
			US-PGPUB;	16:49
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	421	((438/653).CCLS.) and substrate with	USPAT;	2002/09/23
		(trench gap via cavity through hole)	US-PGPUB;	16:49
			EPO; JPO;	
			DERWENT;	
	225	///420/652)	IBM_TDB	0000 (00 (00
_	335	, , , , , , , , , , , , , , , , , , , ,	USPAT;	2002/09/23
		(trench gap via cavity through hole)) and silicon with substrate	US-PGPUB;	16:54
		Silicon with substrate	EPO; JPO;	
ļ			DERWENT; IBM TDB	
_	2	((((438/653).CCLS.) and substrate with	USPAT;	2002/09/23
	_	(trench gap via cavity through hole)) and	US-PGPUB;	16:55
		silicon with substrate) and ground same	EPO; JPO;	
		signal	DERWENT;	
		-	IBM TDB	
-	302		USPAT;	2002/09/23
		(trench gap via cavity through hole)) and	US-PGPUB;	16:55
		silicon with substrate) and barrier	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	149	(((((438/653).CCLS.) and substrate with	USPĀT;	2002/09/23
		(trench gap via cavity through hole)) and	US-PGPUB;	16:38
		silicon with substrate) and barrier) and	EPO; JPO;	
		etch	DERWENT;	
		(420/665) 0070	IBM_TDB	0000 (00 100
-	130	(438/665).CCLS.	USPAT;	2002/09/23
			US-PGPUB;	16:58
			EPO; JPO;	
			DERWENT;	
_	52	///29/66E) CCTC) and	IBM_TDB	2002 (00 (22
-	52	((438/665).CCLS.) and substrate with (trench gap via cavity through hole)	USPAT;	2002/09/23
		(trench gap via cavity through noie)	US-PGPUB;	16:54
			EPO; JPO;	
			DERWENT;	
_	651	(438/687).CCLS.	IBM_TDB	2002/00/22
-	631	(130/00/).ССЦЗ.	USPAT;	2002/09/23
			US-PGPUB;	16:53
			EPO; JPO;]
			DERWENT;	
			IBM_TDB	ţ

-	411	((438/60 CCLS.) and substrate with (trench gap via cavity through hole)	AT; US PGPUB; EPO; JPO;	2002/09/23 16:54
			DERWENT; IBM_TDB	
	281	(((438/687).CCLS.) and substrate with (trench gap via cavity through hole)) and silicon with substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/23 16:55
_	249	((((438/687).CCLS.) and substrate with (trench gap via cavity through hole)) and silicon with substrate) and barrier	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/23 16:55
_	2	(((((438/687).CCLS.) and substrate with (trench gap via cavity through hole)) and silicon with substrate) and barrier) and ground same signal	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/23 16:56
_	71	(((((438/687).CCLS.) and substrate with (trench gap via cavity through hole)) and silicon with substrate) and barrier) and conductive with line	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/23 16:57
-	0	isolation with trench and silicon with substrate with 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/23 16:59
	5033	isolation with trench and silicon with substrate and 438/\$.ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/23 17:00
_	39	(isolation with trench and silicon with substrate and 438/\$.ccls.) and waveguide	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/23 17:06
-	3602	(isolation with trench and silicon with substrate and 438/\$.ccls.) and etch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/23 17:06
-	1738	(isolation with trench and silicon with substrate and 438/\$.ccls.) and etch with substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/23 17:07
-	108	((isolation with trench and silicon with substrate and 438/\$.ccls.) and etch with substrate) and ground and signal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/23 17:07
-	14	("4252862" "5277985" "5539256" "5595937" "5705857" "5719447" "5744394" "5903053" "5909635" "5976986" "6010966" "6033986" "6054380" "6080529").PN.	USPAT	2002/09/23 17:43
-	5	("5516579" "5525837" "5607722" "5641985" "5659057").PN.	USPAT	2002/09/23
_	12	5903053.URPN. 	USPAT USPAT	2002/09/23 17:44 2002/09/23
		"5132775" "5272376" "5298687" "5326412" "5382447" "5545927").PN.		17:46
-	3	5705857.URPN.	USPAT	2002/09/23
	. 9	5429978.URPN.	USPAT	2002/09/23 17:49

			_	
	17	("48946 "5065273 "5214603" "5292678" "5336629" "5343354" "5348905" "5378907" "5384277" "5389559" "5395786" "5429978" "5661057"	AT	2002/09/24 09:52
-	0	"5670805" "5753526").PN. cupper with isolation with trench and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/25
	5	("5208175" "5372963" "5534455"	IBM_TDB USPAT	2002/09/24
_		"5547884" "5589412").PN. copper with isolation with trench and	USPAT;	09:54 2002/09/24
		438/\$.ccls.	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	09:57
_	7	copper with gate same isolation with trench and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/24 09:58
_	11	5909044.URPN.	USPAT	2002/09/24 09:57
_	1	copper with ground and isolation with trench and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/24
	3	copper with line same isolation with trench and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/25 12:37
_	360	waveguide with trench	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/24
-	174	waveguide with trench	IBM_TDB USPAT	2002/09/24
-	3	("3425879" "5094973" "5104824").PN.	USPAT	2002/09/24
-	1	5783844.URPN.	USPAT	2002/09/24 10:14
-	58	waveguide and trench and barrier and oxide and copper	USPAT	2002/09/24 10:26
_	106	silicon with substrate and oxide with substrate and barrier with oxide and barrier with metal and metal with copper	USPAT	2002/09/24
-	35	and etch and silicide (silicon with substrate and oxide with substrate and barrier with oxide and barrier with metal and metal with copper and etch and silicide) and trench	USPAT	2002/09/24 11:11
-	2	gate with polysilicon with copper same high with temperature	USPAT	2002/09/24 11:14
-	0	gate with polysilicon with copper with cost	USPAT	2002/09/24 11:13
-	0	gate with polysilicon with copper with improve	USPAT	2002/09/24 11:13
_	98	gate with polysilicon with copper	USPAT	2002/09/24 11:52
_	2648	silicide with silicon with nitride	USPAT	2002/09/24
_	1399	silicide with silicon with nitride and 438/\$.ccls.	USPAT	2002/09/24
_	705	silicide with silicon with nitride and 438/6\$2.ccls.	USPAT	2002/09/24 12:04

0		TAT	2002/09/24
			12:05
2	silicide with spacer with copper	USPAT	2002/09/24
			13:21
0	silicide with copper and sinane	USPAT	2002/09/24
			13:22
176	silicide with copper and silane	USPAT	2002/09/24
			13:22
5	silicide with copper and silane and	USPAT	2002/09/24
			13:24
20		USPAT	2002/09/24
			13:26
30	copper with silicide with nitride with	USPAT	2002/09/24
	adhesion		13:29
1	5,447,887.pn.	USPAT	2002/09/24
	•		13:34
1	6255698.pn.	USPAT	2002/09/24
	•		14:08
312	thermal with evaporation with CVD	USPAT	2002/09/24
	•		14:09
104	thermal with evaporation with CVD and	USPAT	2002/09/24
	438/\$.ccls.		14:11
35	·	USPAT	2002/09/24
	CVD and 438/\$.ccls.		14:11
35	thermal adj evaporation with CVD and	USPAT	2002/09/24
	438/\$.ccls.		14:15
0		USPAT	2002/09/25
	(cost improve)		09:41
	176 5 20 30 1 1 312 104 35	gate silicide with spacer with copper silicide with copper and sinane silicide with copper and silane silicide with copper and silane silicide with copper and silane and copper with evaporation copper with silicide and 438/655.ccls. copper with silicide with nitride with adhesion s,447,887.pn. fe255698.pn. thermal with evaporation with CVD thermal with evaporation with CVD and 438/\$.ccls. thermal with thermal adj evaporation with CVD and 438/\$.ccls. thermal adj evaporation with CVD and 438/\$.ccls. thermal adj evaporation with CVD with	gate silicide with spacer with copper USPAT 0 silicide with copper and sinane USPAT 176 silicide with copper and silane USPAT 5 silicide with copper and silane and copper with evaporation copper with silicide and 438/655.ccls. USPAT 30 copper with silicide with nitride with adhesion 1 5,447,887.pn. USPAT 1 6255698.pn. USPAT 1 6255698.pn. USPAT 104 thermal with evaporation with CVD USPAT 105 thermal with thermal adj evaporation with CVD and 438/\$.ccls. thermal with thermal adj evaporation with CVD and 438/\$.ccls. 35 thermal adj evaporation with CVD and 438/\$.ccls. thermal adj evaporation with CVD and 438/\$.ccls.